

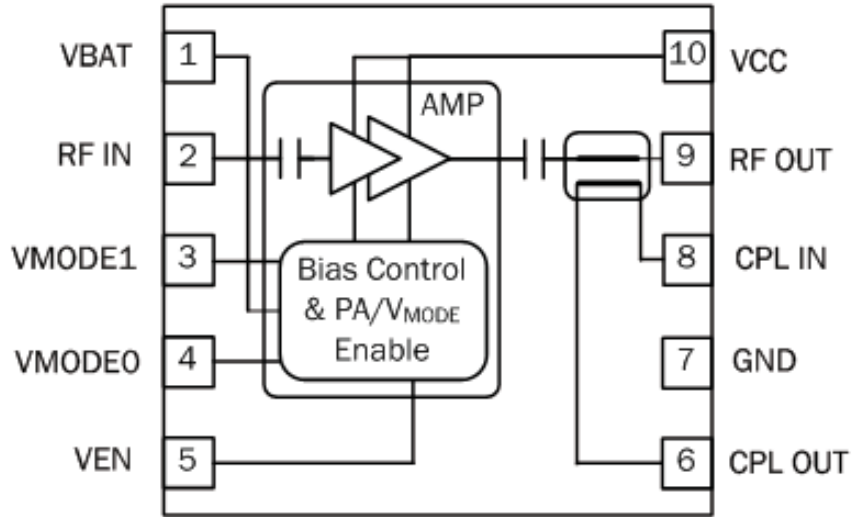


**Features**

- Multi-Mode LTE/UMTS/CDMA
- LTE/UMTS Bands 3, 4, 9, and 10
- CDMA Band Class 15
- LTE PA Efficiency 38%, +28dBm
- Best-in-Class Current Consumption
- Optimized use with DC-DC converter Operation
- Three Power States with Digital Control Interface
- Integrated Power Coupler
- Integrated Blocking and Decoupling Capacitors

**Applications**

- LTE/UMTS/CDMA Wireless Handsets and Datacards



Functional Block Diagram

**Product Description**

The RF7303 is a high-power, high-efficiency linear power amplifier designed for use as final amplification stage in a 3V, 50Ω LTE/UMTS/CDMA mobile cellular equipment. This PA is developed for the E-UTRAN/LTE Bands within the 1710MHz to 1785MHz and along with CDMA Band 15 (BC15) that operates within the 1710MHz to 1755MHz frequency band. The RF7303 has two digital control pins to select one of three power bias states to optimize performance and current drain at lower power levels. The part also has an integrated directional coupler which eliminates the need for an external discrete coupler at the output. The RF7303 meets spectral linearity requirements for CDMA, HSDPA, HSUPA, and fully capable of LTE data transmission. The RF7303 part assembled in a 10-pin, 3mm x 3mm module.

**Ordering Information**

RF7303                      3V WCDMA/CDMA B3 Linear PA Module  
 RF7303PCBA-410      Fully Assembled Evaluation Board

**Optimum Technology Matching® Applied**

- |                                               |                                      |                                     |                                   |
|-----------------------------------------------|--------------------------------------|-------------------------------------|-----------------------------------|
| <input type="checkbox"/> GaAs HBT             | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET          | <input type="checkbox"/> Si BiCMOS   | <input type="checkbox"/> Si CMOS    | <input type="checkbox"/> RF MEMS  |
| <input checked="" type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT    | <input type="checkbox"/> Si BJT     | <input type="checkbox"/> LDMS     |

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# RF7303



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